



DMTH6010SPS

60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

performance.

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C (Note 9)
60V	8mΩ @ V _{GS} = 10V	100A

This new generation N-Channel Enhancement Mode MOSFET is

designed to minimize R_{DS(ON)} and yet maintain superior switching

Features

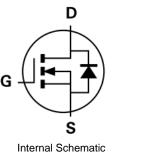
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

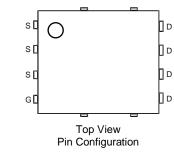
Mechanical Data

- Case: PowerDl[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Bottom View





Ordering Information (Note 4)

Description and Applications

Motors, Lamps and Solenoid Control

Ultra High Performance Power Switching

Transmission Control

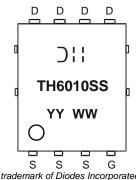
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Part Number	Case	Packaging
DMTH6010SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



) | | = Manufacturer's Marking TH6010SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

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Document number: DS39425 Rev. 3 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 5)	T _A = +25°C T _A = +70°C	ID	13.5 10.4	A
Continuous Drain Current (Notes 6 & 9)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	100 75	- A
Maximum Continuous Body Diode Forward Current (Note 6)		Is	100	А
Pulsed Continuous Body Diode Forward Current (10µs Pulse, Dut	y Cycle = 1%)	I _{SM}	400	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	400	A	
Avalanche Current, L = 0.1mH		I _{AS}	20	А
Avalanche Energy, L = 0.1mH		E _{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	·	R _{0JA}	57	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	167	W
Thermal Resistance, Junction to Case (Note 6)	·	R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

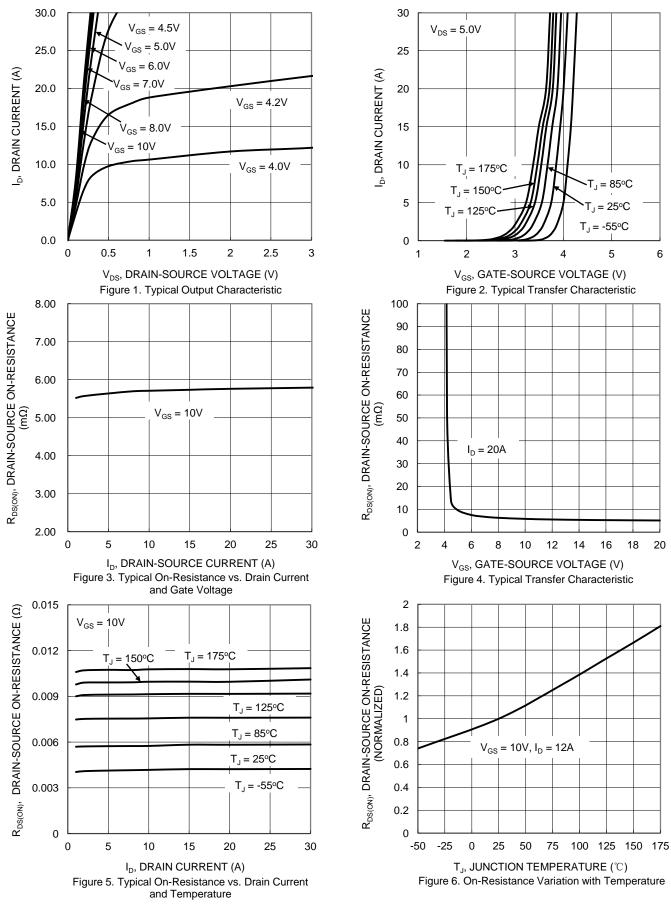
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)					1		
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						÷	
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	6.3	8	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	—	2841	—		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	—	690	—	pF		
Reverse Transfer Capacitance	Crss	—	46	—			
Gate Resistance	Rg	_	0.55	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	38.1	_			
Gate-Source Charge	Q _{gs}	_	8.3	_	nC	$V_{DS} = 30V, I_D = 20A, V_{GS} = 10V$	
Gate-Drain Charge	Q _{gd}		9.3	_			
Turn-On Delay Time	t _{D(ON)}	_	8.6	_			
Turn-On Rise Time	t _R		8.2	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_D = 20A, R_G = 3\Omega$	
Turn-Off Delay Time	t _{D(OFF)}		17.4	_	ns		
Turn-Off Fall Time	t _F	_	5.7				
Body Diode Reverse Recovery Time	t _{RR}		33.8		ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	35.6		nC	I _F = 20A, di/dt = 100A/μs	

Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.
Limited by package.

Notes:



DMTH6010SPS







100 125 150 175

f = 1MHz

75

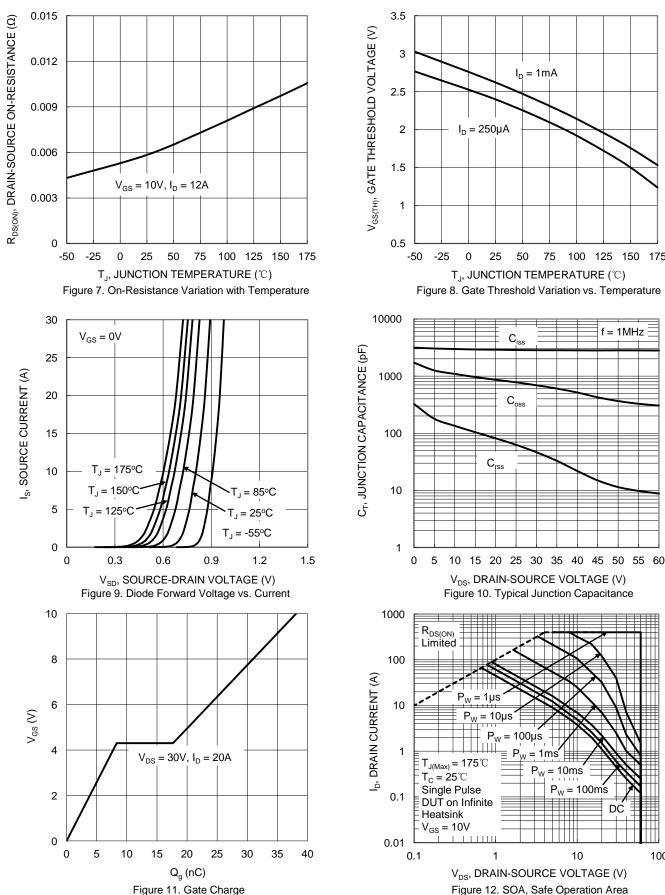
1ms

= 10ms

 $P_w = 100 ms$

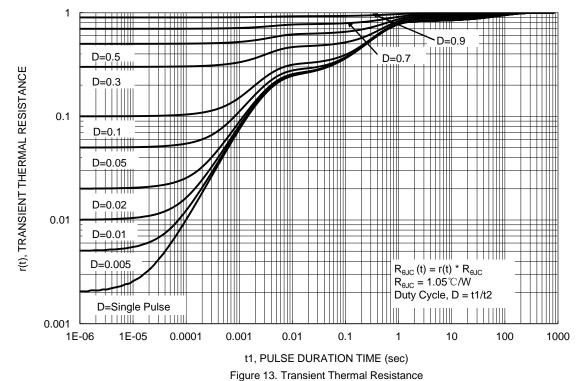
10

DC



100



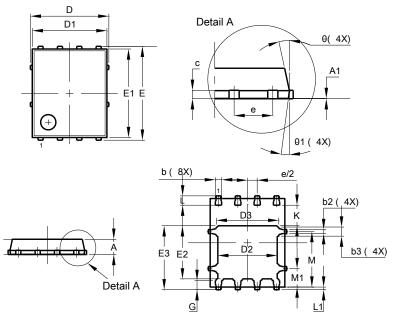




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

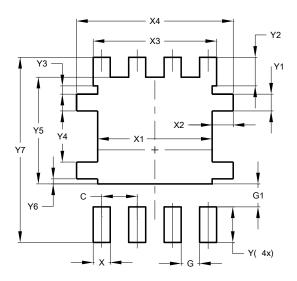


	PowerDI5060-8					
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90 4.30 4.1					
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
Al	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
¥7	6.610			



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